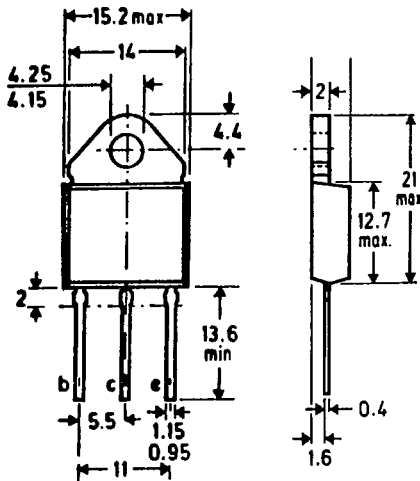


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SILICON PNP EPITAXIAL PLANAR

MECHANICAL DATA

Dimensions in mm



FEATURES

- VERY LOW SATURATION RESISTANCE
- HIGH GAIN AT HIGH CURRENT
- VERY FAST SWITCHING
- NPN COMPLEMENT BUP 32

SOT 93

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector-base voltage ($I_E = 0$)	-60V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-30V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-6V
I_C	Collector current	-30A
P_{tot}	Total power dissipation at $T_{CASE} \leq 25^\circ C$	-60W
T_{stg}	Storage temperature	-55 to 150°C
T_J	Junction temperature	150°C

SEMELAB LTD., TELEPHONE (04555) 4711. TELEX: 341927. FAX: (04555) 4712

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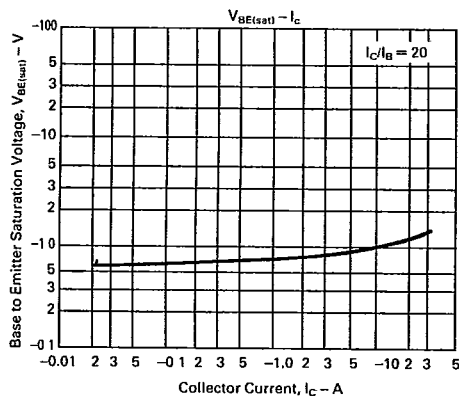
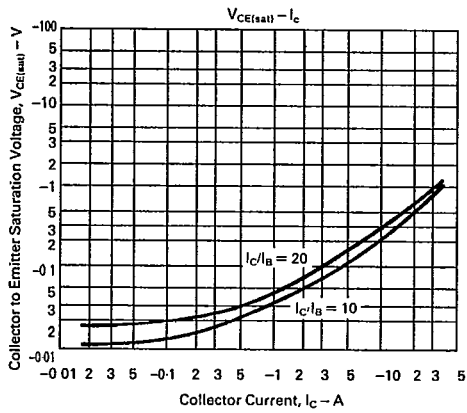
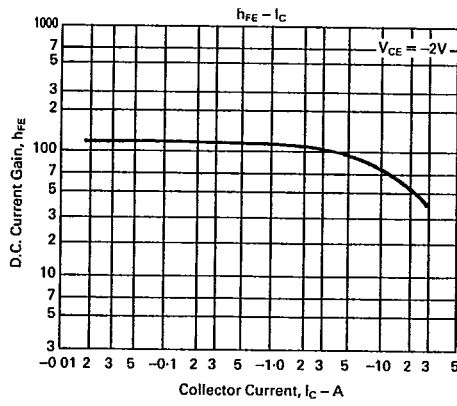
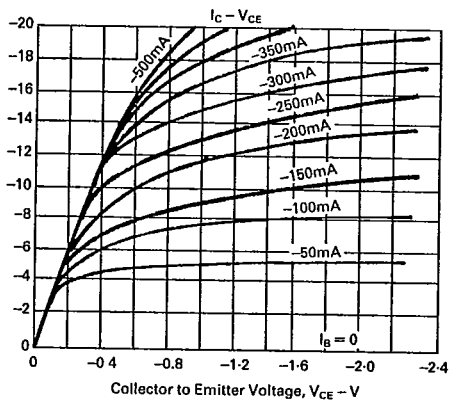
ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ unless otherwise specified)

Parameter	Test Conditions	Min.	Typ.	Max	Unit	
I_{CBO}	Collector cutoff current ($I_E = 0$)	$V_{CB} = -40V$		-100	μA	
I_{EBO}	Emitter cutoff current ($I_C = 0$)	$V_{EB} = -4V$		-100	μA	
$V_{CE(sat)}^*$	Collector-emitter saturation voltage	$I_C = -30A$	$I_B = -1A$	-2	V	
$V_{BE(sat)}^*$	Base emitter voltage	$I_C = -30A$	$I_B = -1A$	-1.4	V	
h_{FE1}^*	DC Current gain	$I_C = -1A$	$V_{CE} = -2V$	70	300	—
h_{FE2}^*		$I_C = -30A$	$V_{CE} = -5V$	30	200	—
f_T	Transition frequency	$I_C = -1A$	$V_{CE} = -5V$	150	MHz	
I_{SB}	Second Breakdown Collector current	$V_{CE} = -10V$	$t = 1 \text{ m sec}$	-20	A	

* Pulsed: pulse duration = $300\mu s$, duty cycle = 1.5%

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